

Preliminary

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

2SK3079A

470 MHz Band Amplifier Applications

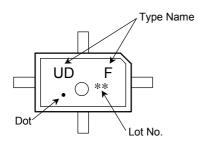
- Output power: $P_0 = 33.50 dBmW (2.2 W) (min)$
- Gain: $G_p = 13.50 dB \text{ (min)}$
- Drain Efficiency: $\eta D = 50.0\%$ (min)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	10	V
Gate-source voltage	V_{GSS}	3	V
Drain current	I _D	3	Α
Power dissipation	P _D (Note 1)	20.0	W
Channel temperature	T _{ch}	150	°C
Storage temperature range	T _{stg}	− 45~150	°C

Note 1: Tc = 25°C

Marking



Unit: mm GATE SOURCE (HEAT SINK) DRAIN **JEDEC** JEITA **TOSHIBA** 2-5N1A

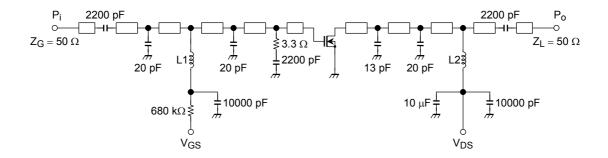
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Output power		Po	V _{DS} = 4.5 V, lidle = 50 mA	33.5	_	_	dBmW
Drain efficiency		η_{D}] (V _{GS} = adjust) f = 470 MHz, P _i = 20dBmW	50.0	_	_	%
Power gain		Gp	$Z_G = Z_L = 50 \Omega$	13.5	_	_	dB
Threshold voltage		V_{th}	$V_{DS} = 4.5 \text{ V}, I_{D} = 0.5 \text{ mA}$	_	0.8	_	V
Drain cut-off current		I _{DSS}	V _{DS} = 10 V, V _{GS} = 0 V	_	_	10	μΑ
Gate-source leakage current		I _{GSS}	V _{GS} = 5 V, V _{DS} = 0 V	_	_	5	μΑ
Load mismatch	(Note 2)		V_{DS} = 5 V, f = 470 MHz, P_i = 20dBmW, P_0 = 33.5dBmW (V_{GS} = adjust) VSWR LOAD 10:1 all phase	No degradation		_	

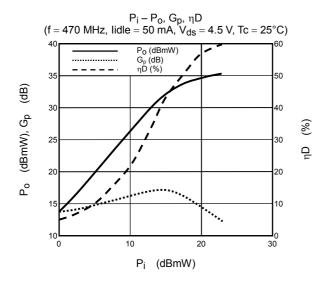
Caution: This is transistor the electrostatic sensitive device. Please handle with caution.

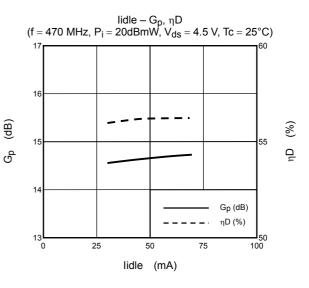
Note 2: When the RF output power test fixture is used

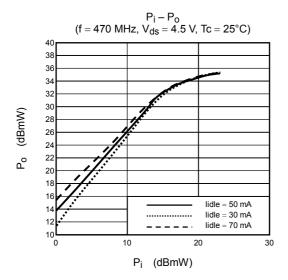
Test Circuit

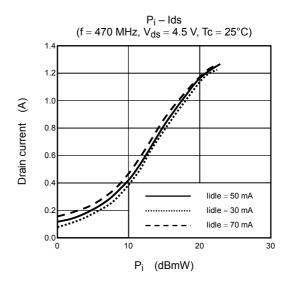


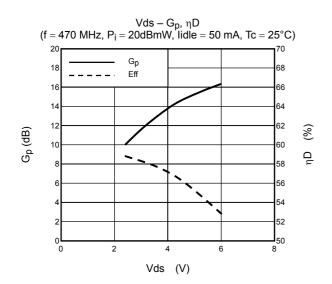
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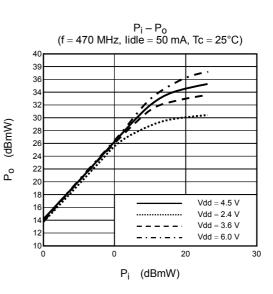




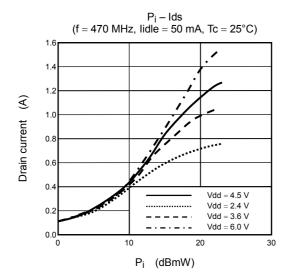








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Caution: These are typical curves and devices are not necessarily guaranteed at these curves.

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